

PATENT Attorney Docket No. ASC-049C1

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

APPLICANT(S):

Fitzgerald

CONFIRMATION NO.

SERIAL NO.:

10/774,890

GROUP NO.:

FILING DATE:

February 9, 2004

EXAMINER:

Tran, Mai Huong C.

2818

TITLE:

RELAXED SIGE PLATFORM FOR HIGH SPEED CMOS

ELECTRONICS AND HIGH SPEED ANALOG CIRCUITS

CERTIFICATE OF FIRST CLASS MAILING UNDER 37 C.F.R. 1.8

I hereby certify that this correspondence, and any document(s) referred to as enclosed herein, is/are being deposited with the United States Postal Service as first class mail, postage prepaid, in an envelope addressed to Mail Stop Amendment, Commissioner of Palents, P.O. Box 1450, Alexandria, VA 22313-1450 on this 17th day of August, 2006.

nda M. Penta

Mail Stop Amendment Commissioner for Patents P.O. Box 1450 Alexandria, VA 22313-1450

Sir:

Submitted herewith is/are:

- 1. Transmittal Form (1 page);
- 2. Second Supplemental information Disclosure Statement (2 pgs.);
- Form USPTO-1449 (1 pg.);
- 4. Copies of cited references C166-C173); and
- Return receipt postcard.

			Application	Serial Number	10/77	4,890		
			Filing Date		Febru	February 9, 2004		
TRANSMITTAL FORM			First Named	First Named Inventor		Fitzgerald		
			Group Art Unit		2818	2818		
			Examiner N	Examiner Name		Fitzgerald		
				Attorney Docket No.		ASC-049C1		
			Patent No.			Not applicable		
			Issue Date			Not applicable		
			issue Date		Not a	Not applicable		
ENCLOSURES (check all that apply)								
☐ Fee	Transmittal Form		Copy of Notic Parts of Appli	e to File Missing		Notice of Appeal to Board of Patent Appeals and Interferences		
	☐ Check Attached☐ Copy of Fee Transmittal Form	_	Formal Drawi			Appeal Brief (in triplicate)		
O	Amendment/Response		Request For C Examination (Status Inquiry		
	☐ Preliminary ☐ After Final		Transmittal			Return Receipt Postcard		
	Affidavits/declaration(s) Letter to Official Draftsperson including Drawings [Total Sheets]		Power of Attorney (Revocation of Prior Powers)		⊠	Certificate of First Class Mailing under 37 C.F.R. 1.8		
			Terminal Disclaimer			Certificate of Facsimile Transmission under 37 C.F.R. 1.8		
	Petition for Extension of Time			aration and Power r Utility or Design tion		Additional Enclosure(s) (please identify below)		
⊠	Supplemental Information Disclosure Statement		Small Entity S	tatement				
	Form PTO-1449 Copies of SIDS Citations (C166-173)		CD(s) for large table or computer program					
	Certified Copy of Priority Document(s) Sequence Listing submission Paper Copy/CD Computer Readable Copy Statement verifying identity of above		Amendment After Allowance Request for Certificate of Correction Certificate of Correction (in duplicate)					
CORRESPONDENCE ADDRESS				SIGNATURE BLOCK				
Direct all correspondence to: Patent Administrator Goodwin Protect LLP Exchange Place Boston, MA 02109 Tel. No.: (617) 520-101 Fax No.: (617) 523-122 Customer No. 051414			1000	Date: August 17, 2006 Reg. No. 44,381 Fel. No.: (617) 570-1806 Pax No.: (617) 523-1231 Code With Procedure LP Exchange Place Boston, MA 02109		Natasha C. Us Attorney for the Applicant Goodwin Procter LLP Exchange Place		

EFS-Web Receipt date: 08/21/2006



PATENT Attorney Docket No. ASC-049C1

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

APPLICANT(S): Fitzgerald

SERIAL NO.: 10/774,890 GROUP NO.: 2818

FILING DATE: February 9, 2004 EXAMINER: TRAN, MAI HUONG C.

TITLE: RELAXED SIGE PLATFORM FOR HIGH SPEED CMOS

ELECTRONICS AND HIGH SPEED ANALOG CIRCUITS

Mail Stop Amendment Commissioner for Patents P.O. Box 1450 Alexandria, VA 22313-1450

SECOND SUPPLEMENTAL INFORMATION DISCLOSURE STATEMENT

Sir:

In accordance with the provisions of 37 C.F.R. 1.97 and 1.98, Applicants hereby make of record the publications listed on the accompanying Form PTO-1449, and other information contained herein, for consideration by the Examiner in connection with the examination of the above-identified patent application. In accordance with 37 C.F.R. 1.98(a)(2), only copies of the non-patent publications are enclosed

REMARKS

In accordance with the provisions of 37 C.F.R. 1.97, this statement is being filed (CHECK ONE):

(1)	within three (3) months of the filing date of a national application other than a continued prosecution application under 37 C.F.R. 1.53(d), or within three (3) months of the date of entry of the national stage as set forth in 37 C.F.R. 1.491 in an international application, or before the mailing of the first Office action on the merits, or before the mailing of a first Office action after the filing of a request for continued examination under 37 C.F.R. 1.114; or
(2)	after the period defined in (1) but before the mailing date of a final action or a notice of allowance under 37 C.F.R. 1.311, and
	the requisite Statement is below, OR
	the requisite fee under 37 C.F.R. 1.17(p), namely \$180.00, is included herein, or

Supplemental Information Disclosure Statement Serial No. 10/774.890 Page 2 of 2 (3) after the mailing date of a final action or notice of allowance but before the payment of the issue fee, AND П the requisite Statement is below, AND П the requisite petition fee under 37 C.F.R. 1.17(p), namely \$180.00 is included herein. It is respectfully requested that each of the publications listed on the attached Form PTO-1449, and other information contained herein, be made of record in this application. STATEMENT As required under 37 C.F.R. 1.97(e), Applicant(s), through the undersigned, hereby state either that [check the appropriate space only if either (2) or (3) is checked on the previous page and the Statement is required]: Each item of information contained in the Information Disclosure Statement was 1. first cited in any communication from a foreign patent office in a counterpart foreign application not more than three months prior to the filing of the Information Disclosure Statement: or 2. No item of information contained in the Information Disclosure Statement was cited in a communication from a foreign patent office in a counterpart foreign application, and, to the knowledge of the person signing this Statement after making reasonable inquiry, no item of information contained in the Information Disclosure Statement was known to any individual designated in 37 C.F.R. 1.56(c) more than three months prior to the filing of the Information Disclosure Statement. Respectfully submitted, noted ca Date: August 17, 2006 Reg. No. 44,381 Natasha C. Us

Tel. No.: (617) 570-1806 Fax No.: (617) 523-1231 Goodwin Procter LLP Exchange Place Boston, Massachusetts 02109 Customer No. 051414

Attorney for Applicant

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PFS-Web Receipt date: 08/21/2006 AUG 2 1 2000

50RM PTO - 1449 ATTY DOCKET NO.: ASC-049C1 APPLICANT: Fitzgerald SECOND SUPPLEMENTAL INFORMATION DISCLOSURE STATEMENT SERIAL NO.: 10/774.890 FILING DATE: February 9, 2004 EXAMINER: Tran. Mai Huong C. GROUP: 2818 U.S. PATENT DOCUMENTS EXAM. DOCUMENT DATE NAME. CLASS SUR FILING DATE IF INIT. NUMBER CLASS APPROPRIATE OTHER ART, JOURNAL ARTICLES, ETC. EXAM. OTHER DOCUMENTS: (Including Author, Title, Date, Relevant Pages, Place of Publication) INIT. C166 Kubota M., et al. "New SOI CMOS Process with Selective Oxidation," IEEE IEDM TECH, DIG., pp. 814-816, (1986). C167 Ming et al., "Interfacial roughness scaling and strain in lattice mismatched Sig Gens thin films on Si" Applied Physics Letters, Vol. 67, No. 5, July 31, 1995, pp. 629-631. C168 Ming et al., "Microscopic structure of interfaces in Si,-,Ge,/Si heterostructures and superlattices studied by x-ray scattering and fluorescence yield." Physical Review B. Vol. 47, No. 24, pp. 373-81, June 15, 1993.

C169 Nishi et al. "Handbook of Semiconductor Manufacturing Technology," Marcel Dekker AG, New York, NY, 2000, pp. 1-22 C170 O'Neill, et al., "Deep Submicron CMOS Based on Silicon Germanium Technology," Fellow, IEEE Transactions on Electron Devices, Vol. 43, No. 6, June 1996 pp. 911-918. C171 Sugii, et al., "Role of Si1-xGex buffer layer on mobility enhancement in a strained-Si channel metal-oxidesemiconductor field-effect transistor," Central Research Laboratory, Hitachi Ltd. 1-280 Higashi-Koigakuboj, Kokubunji-shi, Tokyo 185-8601 Japan, pp. 2948-2950. unknown date. C172 Vossen et al. "Thin Film Processes II" Academic Press Inc., San Diego, CA, 1991, pp. 370-442. C173 Wolfe et al. "Silicon Processing for the VLSI Era, Volume 1; Process Technology," Lattice Press 1986, pp. 124-160. /Dung A. Le/ (07/14/2008) EXAMINER DATE CONSIDERED

ALL REFERENCES CONSIDERED EXCEPT WHERE LINED THROUGH. /DIe/ (07/14/2008)

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